

Mohamed Henini

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784 papers	12,781 citations	53 h-index	86 g-index
878 ext. papers	13,570 ext. citations	3 avg, IF	5.82 L-index

#	Paper	IF	Citations
784	Carrier thermal escape and retrapping in self-assembled quantum dots. <i>Physical Review B</i> , 1999 , 60, 8276-8283	5.3	292
783	Photodegradation of organic pollutants RhB dye using UV simulated sunlight on ceria based TiO ₂ nanomaterials for antibacterial applications. <i>Scientific Reports</i> , 2016 , 6, 38064	4.9	277
782	Two dimensional electrons in a lateral magnetic superlattice. <i>Physical Review Letters</i> , 1995 , 74, 3009-3012	7.4	246
781	Real-time scanning Hall probe microscopy. <i>Applied Physics Letters</i> , 1996 , 69, 1324-1326	3.4	207
780	Paramagnetic Meissner effect in small superconductors. <i>Nature</i> , 1998 , 396, 144-146	50.4	204
779	Probing the hole dispersion curves of a quantum well using resonant magnetotunneling spectroscopy. <i>Physical Review Letters</i> , 1991 , 66, 1749-1752	7.4	199
778	Resonant tunneling through the bound states of a single donor atom in a quantum well. <i>Physical Review Letters</i> , 1992 , 68, 1754-1757	7.4	197
777	Temperature dependence of the optical properties of InAs/Al _{0.1} Ga _{0.9} As self-organized quantum dots. <i>Physical Review B</i> , 1999 , 59, 5064-5068	3.3	196
776	Resistance resonance effects through magnetic edge states. <i>Physical Review Letters</i> , 2000 , 84, 2231-4	7.4	191
775	Magnetic field studies of elastic scattering and optic-phonon emission in resonant-tunneling devices. <i>Physical Review B</i> , 1989 , 39, 3438-3441	3.3	181
774	Magnetoresistance of a two-dimensional electron gas due to a single magnetic barrier and its use for nanomagnetometry. <i>Applied Physics Letters</i> , 1999 , 74, 2507-2509	3.4	178
773	Rare earth element (REE) lanthanum doped zinc oxide (La: ZnO) nanomaterials: Synthesis structural optical and antibacterial studies. <i>Journal of Alloys and Compounds</i> , 2017 , 723, 1155-1161	5.7	166
772	A one-dimensional chain state of vortex matter. <i>Nature</i> , 2001 , 414, 728-31	50.4	159
771	Imaging the electron wave function in self-assembled quantum dots. <i>Science</i> , 2000 , 290, 122-4	33.3	157
770	Fermi-edge singularity in resonant tunneling. <i>Physical Review Letters</i> , 1994 , 72, 2061-2064	7.4	148
769	Electron-concentration-dependent quantum-well luminescence: Evidence for a negatively charged exciton. <i>Physical Review B</i> , 1995 , 51, 7969-7972	3.3	145
768	Spin Excitations of a Two-Dimensional Electron Gas in the Limit of Vanishing Landé Factor. <i>Physical Review Letters</i> , 1996 , 77, 4604-4607	7.4	132

767	Magnetoresistance of a two-dimensional electron gas in a strong periodic potential. <i>Physical Review B</i> , 1990 , 42, 9229-9232	3.3	130
766	High temperature gate control of quantum well spin memory. <i>Physical Review Letters</i> , 2003 , 91, 246601	7.4	125
765	Chaotic electron diffusion through stochastic webs enhances current flow in superlattices. <i>Nature</i> , 2004 , 428, 726-30	50.4	107
764	Resonant magnetotunneling through individual self-assembled InAs quantum dots. <i>Physical Review B</i> , 1996 , 54, 16401-16404	3.3	106
763	Evaluation on La2O3 garlanded ceria heterostructured binary metal oxide nanoplates for UV/visible light induced removal of organic dye from urban wastewater. <i>South African Journal of Chemical Engineering</i> , 2018 , 26, 49-60	3.2	106
762	Acoustic phonon emission from a weakly coupled superlattice under vertical electron transport: observation of phonon resonance. <i>Physical Review Letters</i> , 2006 , 96, 215504	7.4	100
761	Sequential tunneling due to intersubband scattering in double-barrier resonant tunneling devices. <i>Applied Physics Letters</i> , 1988 , 52, 212-214	3.4	97
760	Coherent terahertz sound amplification and spectral line narrowing in a stark ladder superlattice. <i>Physical Review Letters</i> , 2010 , 104, 085501	7.4	92
759	Observation of intrinsic bistability in resonant tunnelling devices. <i>Electronics Letters</i> , 1988 , 24, 1190	1.1	91
758	Temperature dependence of the photoluminescence emission from thiol-capped PbS quantum dots. <i>Applied Physics Letters</i> , 2007 , 90, 101913	3.4	88
757	Probing the wave function of quantum confined states by resonant magnetotunneling. <i>Physical Review B</i> , 1993 , 48, 5664-5667	3.3	87
756	Photoluminescence of negatively charged excitons in high magnetic fields. <i>Physical Review B</i> , 1999 , 59, 2927-2931	3.3	80
755	Probing the quantum states of self-assembled InAs dots by magnetotunneling spectroscopy. <i>Physical Review B</i> , 2002 , 65,	3.3	79
754	Fine structure in magnetization of individual fluxoid states. <i>Physical Review Letters</i> , 2000 , 85, 1528-31	7.4	79
753	Electronic structure of self-assembled InAs quantum dots in GaAs matrix. <i>Applied Physics Letters</i> , 1998 , 73, 1092-1094	3.4	79
752	Observation of giant magnetoresistance due to open orbits in hybrid semiconductor/ferromagnet devices. <i>Physical Review B</i> , 1997 , 55, R16037-R16040	3.3	78
751	Optical anisotropy in arrow-shaped InAs quantum dots. <i>Physical Review B</i> , 1998 , 57, R6815-R6818	3.3	78
750	Scanning Hall probe microscopy of superconductors and magnetic materials. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1996 , 14, 1202		77

- 749 Electronic processes in double-barrier resonant-tunneling structures studied by photoluminescence spectroscopy in zero and finite magnetic fields. *Physical Review B*, **1990**, 41, 10754-10766 3.3 75
- 748 Observation of space-charge bulk-up and thermalisation in an asymmetric double-barrier resonant tunnelling structure. *Journal of Physics Condensed Matter*, **1989**, 1, 10605-10611 1.8 72
- 747 Enhanced spin-relaxation time due to electron-electron scattering in semiconductor quantum wells. *Physical Review B*, **2007**, 75, 3.3 69
- 746 Transition metal titanium (Ti) doped LaFeO₃ nanoparticles for enhanced optical structural and magnetic properties. *Journal of Alloys and Compounds*, **2017**, 712, 870-877 5.7 68
- 745 Charge build-up and intrinsic bistability in an asymmetric resonant-tunnelling structure. *Semiconductor Science and Technology*, **1988**, 3, 1060-1062 1.8 67
- 744 Photocurrent enhancement in hybrid nanocrystal quantum-dot p-i-n photovoltaic devices. *Physical Review Letters*, **2009**, 102, 077402 7.4 66
- 743 Synthesis, structural, magnetic and optical properties of nanocrystalline ZnFe₂O₄. *Physica B: Condensed Matter*, **2011**, 406, 1989-1994 2.8 66
- 742 All-optical measurement of Rashba coefficient in quantum wells. *Physical Review B*, **2008**, 77, 3.3 64
- 741 Energy levels in self-assembled InAs/GaAs quantum dots above the pressure-induced π crossover. *Physical Review B*, **1998**, 58, R4250-R4253 3.3 64
- 740 Gated resonant tunnelling devices. *Electronics Letters*, **1991**, 27, 134 1.1 64
- 739 Photoluminescence spectroscopy of self-assembled InAs quantum dots in strong magnetic field and under high pressure. *Applied Physics Letters*, **1997**, 70, 505-507 3.4 62
- 738 Electrical and spectroscopic studies of space-charged buildup, energy relaxation and magnetically enhanced bistability in resonant-tunneling structures. *Solid-State Electronics*, **1989**, 32, 1101-1108 1.7 60
- 737 The oscillatory magnetoresistance of electrons in a square superlattice potential. *Journal of Physics Condensed Matter*, **1989**, 1, 8257-8262 1.8 58
- 736 Cyclotron resonance in ultra-low-hole-density narrow p-type GaAs/(Al,Ga)As quantum wells. *Physical Review B*, **1997**, 55, 2503-2511 3.3 57
- 735 Observation of spin splitting in single InAs self-assembled quantum dots in AlAs. *Applied Physics Letters*, **1998**, 73, 354-356 3.4 57
- 734 Enhanced magnetic properties of polymer-magnetic nanostructures synthesized by ultrasonication. *Journal of Alloys and Compounds*, **2017**, 720, 395-400 5.7 55
- 733 Carrier localization in GaBiAs probed by photomodulated transmittance and photoluminescence. *Journal of Applied Physics*, **2009**, 106, 023518 2.5 54
- 732 Direct Observation of Melting of the Vortex Solid in Bi₂Sr₂CaCu₂O₈+ δ Single Crystals. *Physical Review Letters*, **1998**, 80, 3610-3613 7.4 53

731	Measuring the Probability Density of Quantum Confined States. <i>Physical Review Letters</i> , 1995 , 75, 1996-1999	3.4	53
730	Temperature dependence of large positive magnetoresistance in hybrid ferromagnetic/semiconductor devices. <i>Applied Physics Letters</i> , 1998 , 72, 1724-1726	3.4	52
729	Role of point defects in the silicon diffusion in GaAs and Al _{0.3} Ga _{0.7} As and in the related superlattice disordering. <i>Journal of Applied Physics</i> , 1992 , 71, 2225-2237	2.5	52
728	Current bistability in double-barrier resonant-tunneling devices. <i>Physical Review B</i> , 1989 , 39, 6205-6207	3.3	52
727	Spin-orbit fields in asymmetric (001)-oriented GaAs/Al _x Ga _{1-x} As quantum wells. <i>Physical Review B</i> , 2011 , 83,	3.3	47
726	Interface induced uniaxial magnetic anisotropy in amorphous CoFeB films on AlGaAs(001). <i>Physical Review Letters</i> , 2008 , 100, 117201	7.4	47
725	Molecular beam epitaxy of GaBiAs on (311)B GaAs substrates. <i>Applied Physics Letters</i> , 2007 , 91, 251909	3.4	47
724	Optical properties and device applications of (InGa)As self-assembled quantum dots grown on (311)B GaAs substrates. <i>Applied Physics Letters</i> , 1998 , 73, 1415-1417	3.4	46
723	Landau-level spectroscopy of a two-dimensional electron system by tunneling through a quantum dot. <i>Physical Review Letters</i> , 2000 , 84, 729-32	7.4	46
722	Structural and optical characterization of self-assembled InAs-GaAs quantum dots grown on high index surfaces. <i>Microelectronics Journal</i> , 1997 , 28, 933-938	1.8	44
721	Oscillatory Dyakonov-Perel spin dynamics in two-dimensional electron gases. <i>Physical Review B</i> , 2007 , 76,	3.3	44
720	Self-sustained current oscillation above 100 GHz in a GaAs/AlAs superlattice. <i>Applied Physics Letters</i> , 1999 , 74, 2179-2181	3.4	44
719	Phonon absorption at the magnetoroton minimum in the fractional quantum Hall effect. <i>Physical Review Letters</i> , 1995 , 74, 2339-2342	7.4	44
718	Piezoelectric effects in In _{0.5} Ga _{0.5} As self-assembled quantum dots grown on (311)B GaAs substrates. <i>Applied Physics Letters</i> , 2000 , 77, 2979-2981	3.4	43
717	Thermopower measurements of the coupling of phonons to electrons and composite fermions. <i>Physical Review B</i> , 1998 , 58, 2017-2025	3.3	42
716	Influence of the As overpressure during the molecular beam epitaxy growth of Si-doped (211)A and (311)A GaAs. <i>Applied Physics Letters</i> , 1995 , 66, 2846-2848	3.4	42
715	Excitation mechanisms of photoluminescence in double-barrier resonant-tunneling structures. <i>Physical Review B</i> , 1990 , 42, 3069-3076	3.3	42
714	Hall anomaly of diffusive magnetic waveguides. <i>Physical Review B</i> , 2003 , 67,	3.3	41

713	Nonradiative exciton energy transfer in hybrid organic-inorganic heterostructures. <i>Physical Review B</i> , 2008 , 77,	3-3	40
712	Piezoelectric-induced quantum-confined Stark effect in self-assembled InAs quantum dots grown on (N11) GaAs substrates. <i>Applied Physics Letters</i> , 2000 , 77, 1982-1984	3-4	40
711	High-temperature light emission from InAs quantum dots. <i>Applied Physics Letters</i> , 1999 , 75, 814-816	3-4	39
710	D- centers probed by resonant tunneling spectroscopy. <i>Physical Review B</i> , 1996 , 53, 9554-9557	3-3	39
709	Even denominator filling factors in the thermoelectric power of a two-dimensional electron gas. <i>Physical Review Letters</i> , 1996 , 76, 3630-3633	7-4	39
708	Distribution of bismuth atoms in epitaxial GaAsBi. <i>Applied Physics Letters</i> , 2011 , 98, 101902	3-4	38
707	Terahertz phonon optics in GaAs/AlAs superlattice structures. <i>Physical Review B</i> , 2003 , 68,	3-3	36
706	Stark shift in electroluminescence of individual InAs quantum dots. <i>Applied Physics Letters</i> , 2000 , 76, 3932-3934	3-4	35
705	Thermal effects in quantum dot lasers. <i>Journal of Applied Physics</i> , 1999 , 85, 625-627	2-5	35
704	Imaging nonequilibrium phonon-induced backscattering in the quantum Hall regime. <i>Physical Review Letters</i> , 1992 , 69, 1684-1686	7-4	35
703	Quantum Hall ferromagnet at high filling factors: A magnetic-field-induced Stoner transition. <i>Physical Review B</i> , 2005 , 72,	3-3	34
702	Magnetophotoluminescence of negatively charged excitons in narrow quantum wells. <i>Physical Review B</i> , 2001 , 63,	3-3	34
701	Magnetoresistance oscillations due to internal Landau band structure of a two-dimensional electron system in a periodic magnetic field. <i>Physical Review B</i> , 2001 , 64,	3-3	34
700	Tailoring the electronic properties of GaAs/AlAs superlattices by InAs layer insertions. <i>Applied Physics Letters</i> , 2002 , 81, 661-663	3-4	34
699	Effect of As overpressure on Si-doped (111)A GaAs grown by molecular beam epitaxy: a photoluminescence study. <i>Semiconductor Science and Technology</i> , 1992 , 7, 1504-1507	1-8	34
698	Carrier thermalization within a disordered ensemble of self-assembled quantum dots. <i>Physical Review B</i> , 2000 , 62, 11084-11088	3-3	33
697	Terahertz response of zero-dimensional states in resonant tunneling diodes. <i>Applied Physics Letters</i> , 1995 , 67, 3453-3455	3-4	33
696	Growth and electrical transport properties of very high mobility two-dimensional hole gases displaying persistent photoconductivity. <i>Applied Physics Letters</i> , 1994 , 65, 2054-2056	3-4	33

695	Improvement of the nutritional quality of foods as a public health tool. <i>Public Health</i> , 2011 , 125, 717-24	4	32
694	Properties and applications of quantum dot heterostructures grown by molecular beam epitaxy. <i>Nanoscale Research Letters</i> , 2006 , 1, 32-45	5	32
693	Strain relaxation in stacked InAs/GaAs quantum dots studied by Raman scattering. <i>Applied Physics Letters</i> , 2003 , 83, 3069-3071	3.4	32
692	Quantum-dot phonons in self-assembled InAs/GaAs quantum dots: Dependence on the coverage thickness. <i>Applied Physics Letters</i> , 2000 , 77, 3556-3558	3.4	32
691	Magnetoresistance and Hall magnetometry of single submicron ferromagnetic structures. <i>Journal of Applied Physics</i> , 2000 , 87, 5986-5988	2.5	31
690	Adsorbed and substituted Sb dimers on GaAs(001). <i>Physical Review B</i> , 1996 , 53, R16148-R16151	3.3	31
689	Surface effects of vapour-liquid-solid driven Bi surface droplets formed during molecular-beam-epitaxy of GaAsBi. <i>Scientific Reports</i> , 2016 , 6, 28860	4.9	30
688	InAs quantum dots grown on nonconventionally oriented GaAs substrates. <i>Journal of Crystal Growth</i> , 1998 , 187, 126-132	1.6	30
687	Nitrogen incorporation into strained (In, Ga) (As, N) thin films grown on (100), (511), (411), (311), and (111) GaAs substrates studied by photoreflectance spectroscopy and high-resolution x-ray diffraction. <i>Journal of Applied Physics</i> , 2006 , 100, 093522	2.5	30
686	Multiple gated InAs dot ensembles. <i>Applied Physics Letters</i> , 1999 , 75, 671-673	3.4	30
685	Resonant magnetotunneling via one-dimensional quantum confined states. <i>Physical Review Letters</i> , 1994 , 73, 1146-1149	7.4	30
684	Radioluminescence and photoluminescence characterization of Eu and Tb doped barium stannate phosphor ceramics. <i>Journal of Alloys and Compounds</i> , 2014 , 590, 417-423	5.7	29
683	Resistance noise scaling in a dilute two-dimensional hole system in GaAs. <i>Physical Review Letters</i> , 2003 , 90, 076402	7.4	29
682	Hybrid magneto-electric states in resonant tunnelling structures. <i>Superlattices and Microstructures</i> , 1989 , 5, 527-530	2.8	29
681	Temperature dependence of the breakdown of the quantum Hall effect studied by induced currents. <i>Physical Review B</i> , 2004 , 70,	3.3	28
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679	Integrated piezoresistive sensors for atomic force-guided scanning Hall probe microscopy. <i>Applied Physics Letters</i> , 2003 , 82, 3538-3540	3.4	28
678	Generation and propagation of monochromatic acoustic phonons in gallium arsenide. <i>Applied Physics Letters</i> , 2002 , 81, 3497-3499	3.4	28

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- 675 Edge channels and the quantum-Hall-effect breakdown. *Physical Review B*, **1994**, 49, 5379-5385 3.3 27
- 674 Zero-dimensional states in macroscopic resonant tunneling devices. *Applied Physics Letters*, **1994**, 64, 2563-2565 3.4 27
- 673 Thermal quenching of single localized excitons in GaInNAs layers. *Applied Physics Letters*, **2011**, 98, 131903 3.4 26
- 672 Dynamic quantum-confined stark effect in self-assembled InAs quantum dots. *Applied Physics Letters*, **2001**, 78, 931-933 3.4 26
- 671 The resistance of two quantum point contacts in series. *Journal of Physics Condensed Matter*, **1989**, 1, 7505-7511 1.8 26
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- 669 Evidence for sequential tunnelling and charge build-up in double barrier resonant tunnelling devices. *Surface Science*, **1988**, 196, 404-409 1.8 26
- 668 Ultrafast strain-induced current in a GaAs Schottky diode. *Physical Review Letters*, **2011**, 106, 066602 7.4 25
- 667 $(2\times 2)/c(2\times 2)$ to $(4\times 4)/c(8\times 8)$ transition on GaAs(001) surfaces. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1996**, 14, 943 25
- 666 Fundamental Relation between Electrical and Thermoelectric Transport Coefficients in the Quantum Hall Regime. *Physical Review Letters*, **1997**, 78, 4621-4624 7.4 25
- 665 Indium interdiffusion in annealed and implanted InAs/(AlGa)As self-assembled quantum dots. *Journal of Applied Physics*, **2001**, 89, 6044-6047 2.5 25
- 664 Influence of high-index GaAs substrates on the growth of highly strained (InGa)As/GaAs heterostructures. *Journal of Crystal Growth*, **1999**, 201-202, 276-279 1.6 25
- 663 Surface acoustic wave attenuation by localized electrons in a 2DEG at a GaAs/AlGaAs heterojunction. *Semiconductor Science and Technology*, **1992**, 7, 641-647 1.8 25
- 662 Subterahertz acoustical pumping of electronic charge in a resonant tunneling device. *Physical Review Letters*, **2012**, 108, 226601 7.4 24
- 661 Luminescence characterization of cerium doped yttrium gadolinium aluminate phosphors. *Optical Materials*, **2012**, 34, 1921-1925 3.3 24
- 660 Advances in self-assembled semiconductor quantum dot lasers. *Microelectronics Journal*, **2005**, 36, 950-958 24

- 659 Suppression of electron channelling in microscopic magnetic waveguides. *Physical Review B*, **2001**, 64, 3.3 24
- 658 Phonoconductivity measurement of the phonon absorption by a two-dimensional hole gas in a GaAs heterojunction. *Physical Review B*, **1996**, 54, 2019-2027 3.3 24
- 657 Energy states of Be in GaAs. *Physical Review B*, **1996**, 53, 12829-12834 3.3 24
- 656 Edge effects in a gated submicron resonant tunneling diode. *Applied Physics Letters*, **1992**, 60, 2508-2510 3.4 24
- 655 Resonant tunnelling studies of magnetoelectric quantisation in wide quantum wells. *Journal of Physics Condensed Matter*, **1989**, 1, 4865-4871 1.8 24
- 654 Band gap and partial density of states for ZnO: Under high pressure. *Journal of Alloys and Compounds*, **2015**, 619, 812-819 5.7 23
- 653 Influence of reaction time and synthesis temperature on the physical properties of ZnO nanoparticles synthesized by the hydrothermal method. *Applied Physics A: Materials Science and Processing*, **2018**, 124, 1 2.6 23
- 652 Solid state synthesis of SrAl₂O₄:Mn²⁺ co-doped with Nd³⁺ phosphor and its optical properties. *Journal of Luminescence*, **2013**, 144, 128-132 3.8 23
- 651 Raman scattering by the E_{2h} and A₁(LO) phonons of In_xGa_{1-x}N epilayers (0.25 Journal of Applied Physics, **2012**, 111, 063502 2.5 23
- 650 Absence of long-range ordered reconstruction on the GaAs(311)A surface. *Physical Review B*, **1997**, 55, 15397-15400 3.3 23
- 649 Electrical rectification by magnetic edge states. *Physica E: Low-Dimensional Systems and Nanostructures*, **2002**, 13, 699-702 3 23
- 648 Spectral analysis of InGaAs/GaAs quantum-dot lasers. *Applied Physics Letters*, **1999**, 75, 2169-2171 3.4 23
- 647 Annealing effects on Si-doped GaAs grown on high-index planes by molecular-beam epitaxy. *Journal of Applied Physics*, **1994**, 75, 3151-3157 2.5 23
- 646 Electroluminescence investigations of electron and hole resonant tunneling in p-i-n double-barrier structures. *Physical Review B*, **1992**, 45, 9513-9516 3.3 23
- 645 Rashba spin-splitting of electrons in asymmetric quantum wells. *Physical Review B*, **2010**, 82, 3.3 22
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- 643 Evidence for quantum states corresponding to families of stable and chaotic classical orbits in a wide potential well. *Physical Review B*, **1995**, 51, 18029-18032 3.3 22
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641	Scanning capacitance imaging of compressible and incompressible quantum Hall effect edge strips. <i>New Journal of Physics</i> , 2012 , 14, 083015	2.9	21
640	Micromachined III-V cantilevers for AFM-tracking scanning Hall probe microscopy. <i>Journal of Micromechanics and Microengineering</i> , 2003 , 13, 124-128	2	21
639	Edge phonon conductivity in a magnetically quantized two-dimensional electron gas. <i>Physical Review B</i> , 1994 , 49, 2585-2594	3.3	21
638	Observation of the transition to an insulating state consistent with a Wigner solid in a high-density 2D hole gas. <i>Physica B: Condensed Matter</i> , 1993 , 184, 95-99	2.8	21
637	Revealing the nature of low-temperature photoluminescence peaks by laser treatment in van der Waals epitaxially grown WS monolayers. <i>Nanoscale</i> , 2018 , 10, 4807-4815	7.7	20
636	Efficient light harvesting in hybrid CdTe nanocrystal/bulk GaAs p-i-n photovoltaic devices. <i>Applied Physics Letters</i> , 2009 , 94, 233502	3.4	20
635	Upconversion electroluminescence in InAs quantum dot light-emitting diodes. <i>Applied Physics Letters</i> , 2008 , 92, 091121	3.4	20
634	Voltage-controlled hole spin injection in nonmagnetic GaAs/AlAs resonant tunneling structures. <i>Physical Review B</i> , 2006 , 73,	3.3	20
633	Electric-field inversion asymmetry: Rashba and Stark effects for holes in resonant tunneling devices. <i>Physical Review B</i> , 2006 , 74,	3.3	20
632	Resonant tunneling and photoluminescence spectroscopy in quantum wells containing self-assembled quantum dots. <i>Journal of Applied Physics</i> , 2000 , 88, 2005-2012	2.5	20
631	Cyclotron resonance of high-mobility GaAs/AlGaAs (311) 2DHGs. <i>Semiconductor Science and Technology</i> , 1993 , 8, 1465-1469	1.8	20
630	Quantum-resolved investigations of flux dynamics: Collective and single vortex effects. <i>Physical Review Letters</i> , 1993 , 71, 3854-3857	7.4	20
629	Hole space-charge buildup and evidence for sequential tunneling in p-type double-barrier resonant tunneling devices. <i>Applied Physics Letters</i> , 1992 , 60, 1474-1476	3.4	20
628	Fabrication of novel transparent Co ₃ O ₄ -TiO ₂ nanowires p-n heterojunction diodes for multiband photodetection applications. <i>Journal of Alloys and Compounds</i> , 2017 , 712, 7-14	5.7	19
627	Disorder-driven intermediate state in the lattice melting transition of Bi ₂ Sr ₂ CaCu ₂ O ₈ +δ single crystals. <i>Physical Review B</i> , 1997 , 56, R14295-R14298	3.3	19
626	Magnetoanisotropy of electron-correlation-enhanced tunneling through a quantum dot. <i>Physical Review B</i> , 2007 , 75,	3.3	19
625	Time-resolved photoluminescence of InAs quantum dots in a GaAs quantum well. <i>Applied Physics Letters</i> , 2004 , 84, 3046-3048	3.4	19
624	Study of electron-hole generation and recombination in semiconductors using the Osaka free electron laser. <i>Physica B: Condensed Matter</i> , 2002 , 314, 431-436	2.8	19

623	Resonant tunnelling at far infra-red frequencies. <i>Journal of Physics Condensed Matter</i> , 1994 , 6, 3945-3954.	1.9	19
622	Visible to infrared low temperature luminescence of Er(3+), Nd(3+) and Sm(3+) in CaSnO ₃ phosphors. <i>Applied Radiation and Isotopes</i> , 2015 , 99, 69-76	1.7	18
621	Raman scattering reveals strong LO-phonon-hole-plasmon coupling in nominally undoped GaAsBi: optical determination of carrier concentration. <i>Optics Express</i> , 2014 , 22, 11680-9	3.3	18
620	Correlations between the band structure, activation energies of electron traps, and photoluminescence in n-type GaNAs layers. <i>Applied Physics Letters</i> , 2012 , 101, 082109	3.4	18
619	Collective cyclotron modes in high-mobility two-dimensional hole systems in GaAs - (Ga, Al)As heterojunctions: I. Experiments at low magnetic fields and theory. <i>Journal of Physics Condensed Matter</i> , 1997 , 9, 3163-3179	1.8	18
618	Probing the intermixing in In(Ga)As/GaAs self-assembled quantum dots by Raman scattering. <i>Journal of Applied Physics</i> , 2006 , 99, 043501	2.5	18
617	Raman scattering in InAs/(AlGa)As self-assembled quantum dots: Evidence of Al intermixing. <i>Applied Physics Letters</i> , 2006 , 88, 141905	3.4	18
616	Nonlinear charging effect of quantum dots in a p-i-n diode. <i>Physical Review B</i> , 2003 , 68,	3.3	18
615	Trion formation in narrow GaAs quantum well structures. <i>Physical Review B</i> , 2005 , 71,	3.3	18
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